

Kesterite Cu₂ZnSnS₄ as a Low Cost Inorganic Hole Transporting Material for High Efficiency Perovskite Solar Cells

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S1. TEM images of CZTS nanoparticles.

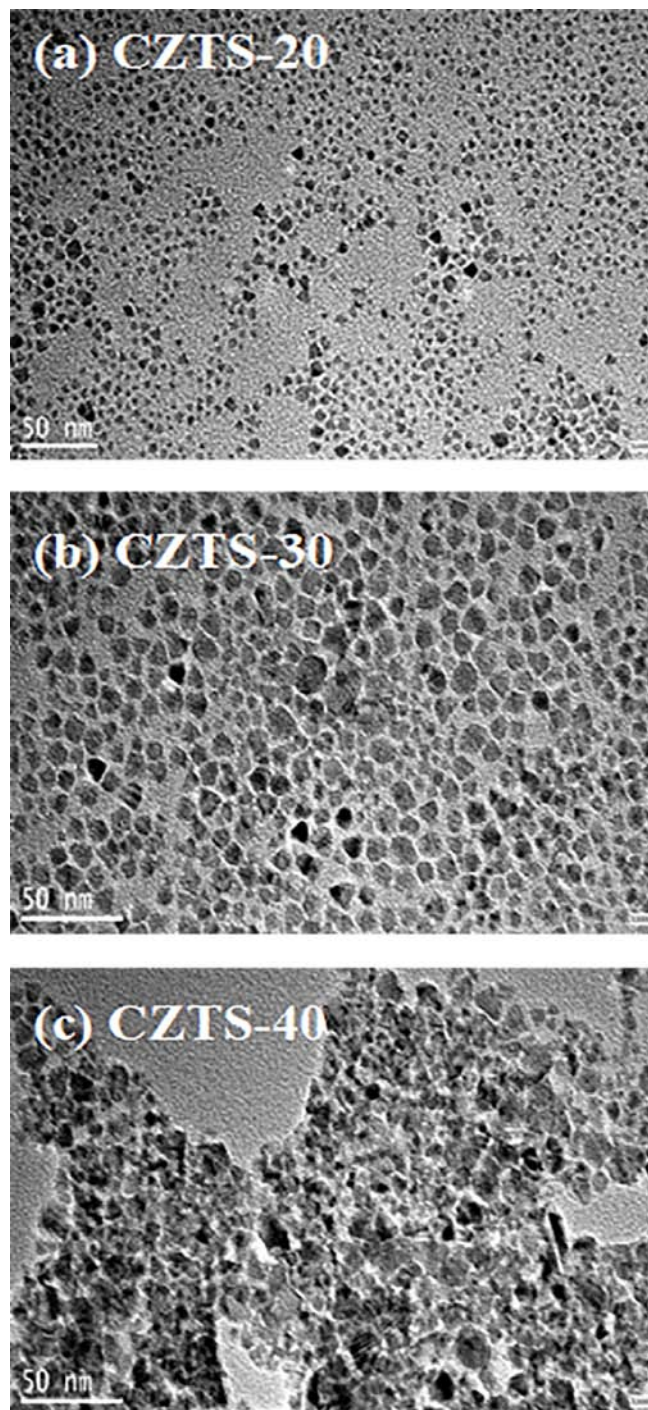


Figure S1. TEM images of CZTS nanoparticles synthesized with reaction time of 20 (a), 30 (b) and 40 (c) minutes, abbreviated as CZTS-20, CZTS-30 and CZTS-40 respectively.

S2. Optimization of the size, spin-coating speed and annealing time of CZTS nanoparticles and dispersion solvent.

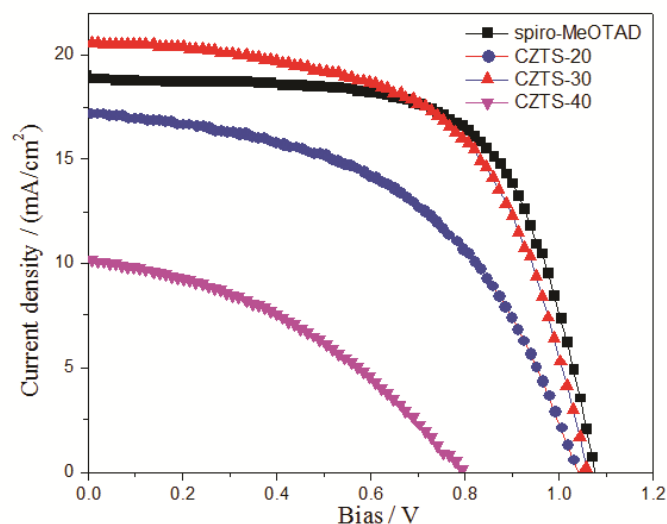


Figure S2. J-V curves of $\text{CH}_3\text{NH}_3\text{PbI}_3$ PSC devices based on CZTS nanoparticles with different sizes or spiro-OMeTAD HTM measured under illumination of an AM 1.5 solar simulator (100 mW cm^{-2}) in air.

Table S1. Photovoltaic parameters of the best $\text{FTO}/\text{TiO}_2/\text{CH}_3\text{NH}_3\text{PbI}_3$ perovskite/HTM/Au PSC devices with different HTMs.

Hole transport material (HTM) ^a	Reaction time (min)	V_{oc} (V)	J_{sc} (mA/cm^2)	FF (%)	PCE (%)
CZTS-20	20	1.04	17.20	50.1	8.94
CZTS-30	30	1.06	20.54	58.7	12.75
CZTS-40	40	0.80	10.16	38.6	3.12
spiro-MeOTAD	-	1.07	18.94	65.0	13.23

^a Annealing temperature is fixed at 100°C .

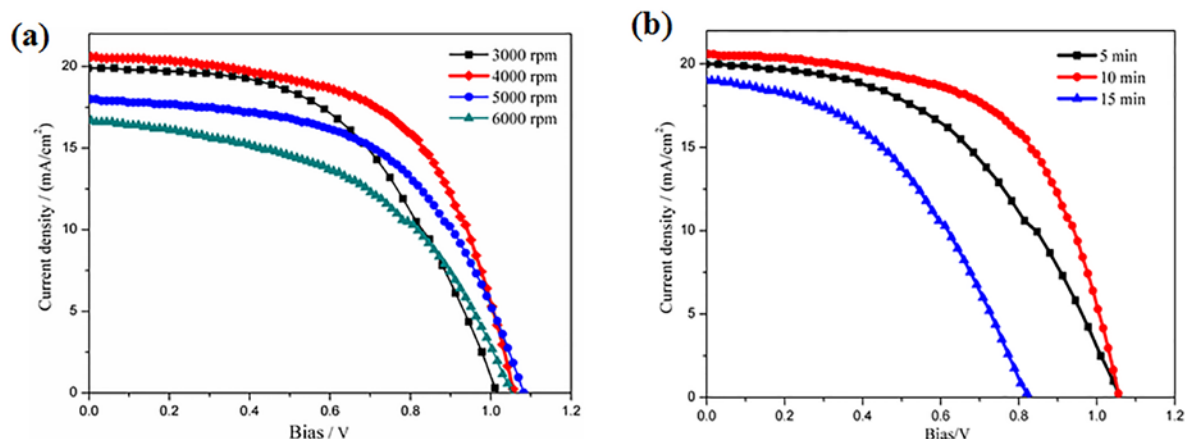


Figure S3. J-V curves of $\text{CH}_3\text{NH}_3\text{PbI}_3$ PSC devices with CZTS-30 HTM prepared with different spin-coating speeds (a) and annealing times (b). The measurements were carried out under illumination of an AM 1.5 solar simulator (100 mW cm^{-2}) in air.

Table S2. Photovoltaic parameters of the best $\text{CH}_3\text{NH}_3\text{PbI}_3$ PSC devices based on CZTS-30 HTM prepared with different spin-coating speeds and annealing times.^[a]

spin-coating speed (rpm)	annealing time (min)	V_{oc} (V)	J_{sc} (mA/cm^2)	FF (%)	PCE (%)
3000 ^b		1.02	19.91	51.7	10.51
4000 ^b	10	1.06	20.54	58.7	12.75
5000 ^b		1.08	17.98	55.2	10.73
6000 ^b		1.05	16.72	49.1	8.61
	5 ^c	1.06	20.00	47.8	10.10
4000	10 ^c	1.06	20.54	58.7	12.75
	15 ^c	0.83	19.02	43.9	6.89

^a Annealing temperature is fixed at 100°C . ^b Annealing time is fixed at 10 min. ^c Spin-coating speed is fixed at 4000 rpm.

Table S3. Photovoltaic parameters of the $\text{CH}_3\text{NH}_3\text{PbI}_3$ PSC devices based on CZTS-30 HTM dispersed in chlorobenzene with different spin-coating speeds.

spin-coating speed (rpm)	annealing time (min)	V_{oc} (V)	J_{sc} (mA/cm^2)	FF (%)	PCE (%)
2000		0.81	1.82	32.59	0.48
3000	10	0.93	6.48	34.64	2.09
4000		0.86	3.46	44.78	1.34

S3. Histograms of PCE, J_{sc} and FF.

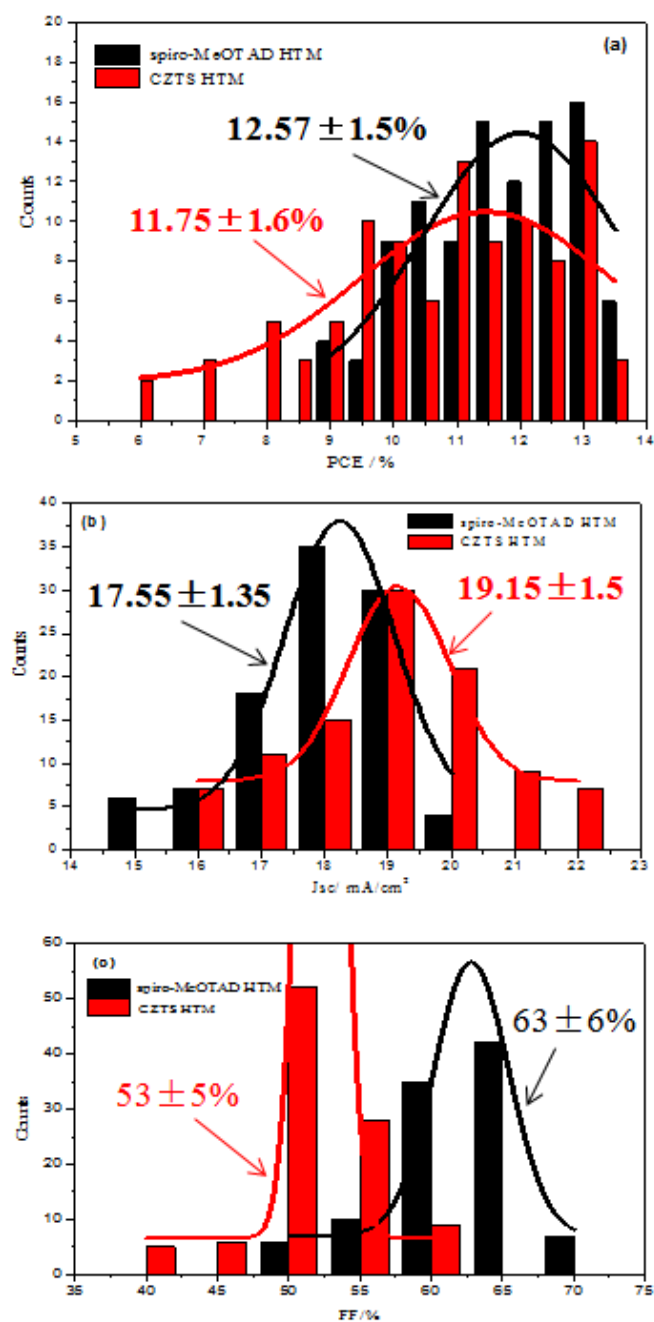


Figure S4. Histograms of PCE (a), J_{sc} (b) and FF (c) for the $CH_3NH_3PbI_3$ perovskite-based PSCs devices with different HTMs.

S4. Hysteresis of J-V curves of the devices with different HTMs.

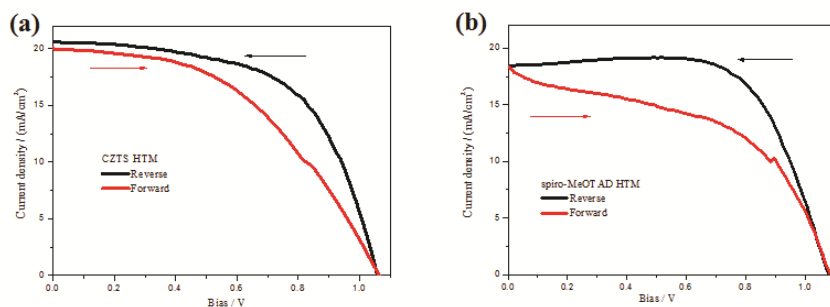


Figure S5. J-V curves of $\text{CH}_3\text{NH}_3\text{PbI}_3$ PSCs devices with CZTS (a) and with spiro-OMeTAD (b) HTM in different scan directions. The measurements were carried out with 0.1 V/s scan rate under AM 1.5 illumination at an irradiation intensity of $100 \text{ mW} \cdot \text{cm}^{-2}$.

Table S4. Photovoltaic parameters of the best $\text{FTO}/\text{TiO}_2/\text{CH}_3\text{NH}_3\text{PbI}_3$ perovskite/HTM/Au PSC devices with different HTMs in different scan directions with 0.1 V/s scan rate.

HTM	Scan direction	V_{oc} (V)	J_{sc} (mA/cm^2)	FF (%)	PCE (%)	Hysteresis of PCE ^a
CZTS	Reverse	1.06	20.54	59.7	12.75	22.4%
	Forward	1.06	19.94	46.7	9.90	
spiro-MeOTAD	Reverse	1.08	18.51	67.6	13.51	28.3%
	Forward	1.08	18.49	48.5	9.69	

^a Hysteresis of PCE = $[\text{PCE}(\text{reverse}) - \text{PCE}(\text{forward})]/\text{PCE}(\text{reverse})$

S5. Stabilized power output for the devices with different HTMs.

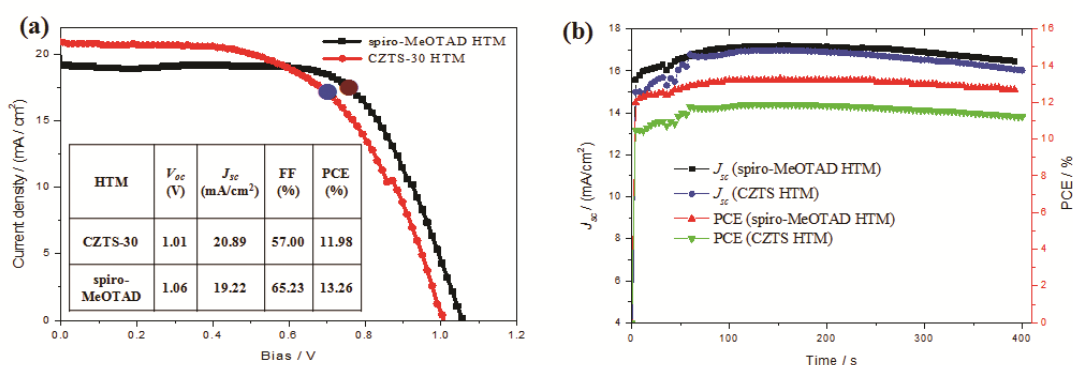


Figure S6. (a) J-V curves of $\text{CH}_3\text{NH}_3\text{PbI}_3$ PSC devices with CZTS-30 or spiro-MeOTAD HTM measured under illumination of an AM 1.5 solar simulator (100 mW cm^{-2}) in air. The maximum power point is 0.70 and 0.76 V for CZTS-30 and spiro-MeOTAD, respectively. (b) Photocurrent density (J_{sc}) and power conversion efficiency (PCE) as a function of time for the device held at 0.70 V (CZTS) or 0.76 V (spiro-MeOTAD) forward bias.

S6. PL spectra of $\text{CH}_3\text{NH}_3\text{PbI}_3$ perovskite films coated by CZTS nanoparticles.

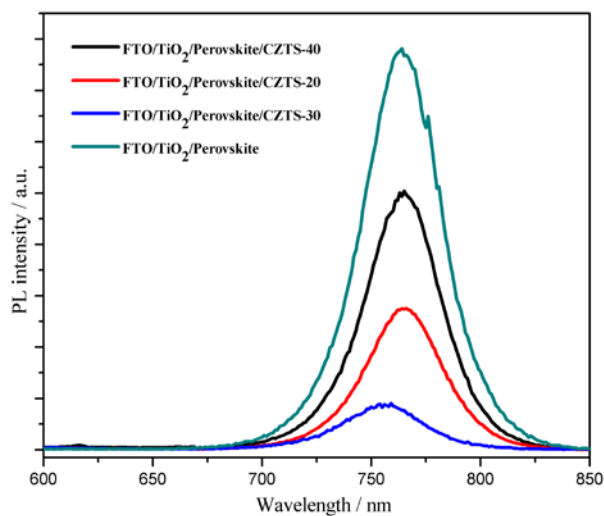


Figure S7. PL spectra of $\text{CH}_3\text{NH}_3\text{PbI}_3$ perovskite films with and without CZTS nanoparticles with different sizes.

S7. AFM images of the perovskite/CZTS and perovskite/spiro-MeOTAD films.

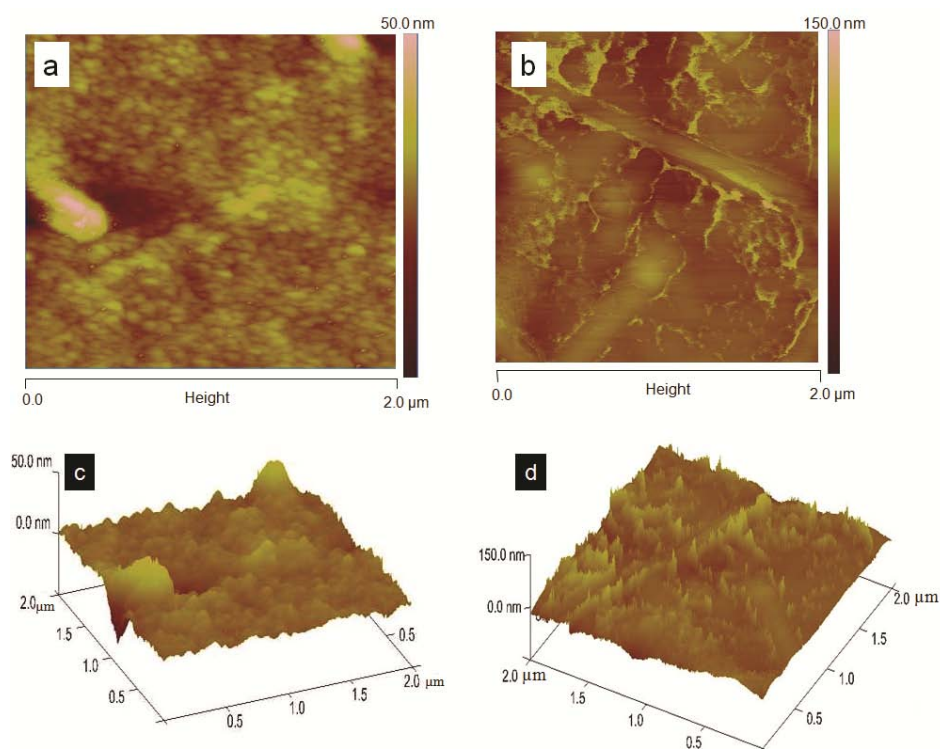


Figure S8. 2D and 3D AFM images of the perovskite/CZTS (a, c) and perovskite/spiro-MeOTAD (b, d) films.

S8. XRD patterns of $\text{CH}_3\text{NH}_3\text{PbI}_3$ perovskite films with or without CZTS HTM.

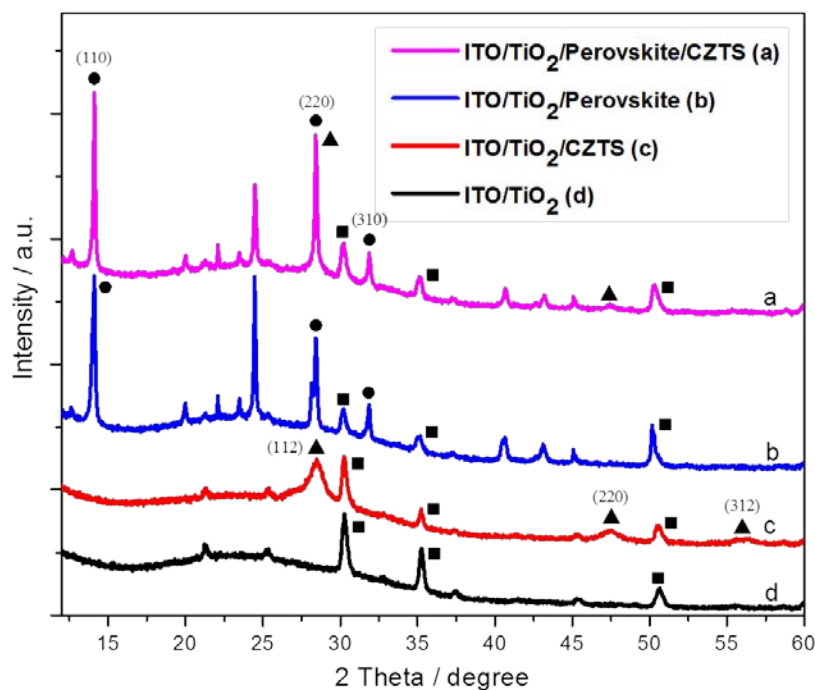


Figure S9. XRD patterns of $\text{CH}_3\text{NH}_3\text{PbI}_3$ perovskite films with or without CZTS film. The filled circle, triangle and square mark the characteristic diffraction peaks of $\text{CH}_3\text{NH}_3\text{PbI}_3$ perovskite, CZTS and TiO_2 , respectively.

S9. Impedance spectra of the devices under different biases.

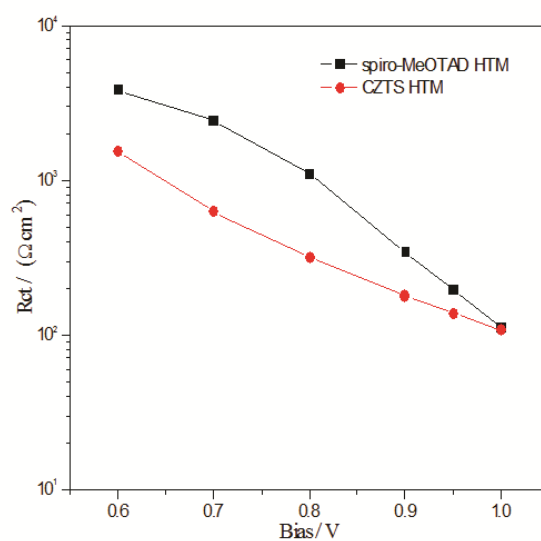


Figure S10. Recombination resistance (R_{rec}) of the devices with different HTMs at different biases.